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(54) **Organic light-emitting display system and method of manufacturing the same**

Organisches lichtemittierendes Anzeigesystem und Verfahren zu seiner Herstellung

Système d'affichage électroluminescent organique et son procédé de fabrication

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Description

BACKGROUND

Technological Field

[0001] The disclosed technology relates to an organic light-emitting display system and a method of manufacturing the same, and more particularly, to an organic light-emitting display system and manufacturing method which enhances the sealing force of a thin film encapsulation layer surrounding the light-emitting portion of the display system.

Description of the Related Technology

[0002] An organic light-emitting display system includes an organic light-emitting device or diode (OLED) including a hole injection electrode, an electron injection electrode, and an organic light-emitting layer formed between the hole injection electrode and the electron injection electrode. Such a display system is self-emissive system in that light is emitted when excitons, which are generated when electrons injected from the hole injection electrode and electrons injected from the electron injection electrode combine with each other in the organic light-emitting layer, decay from an excited state to a ground state.

[0003] Since an OLED display system does not require a separate light source, it can operate at a low voltage and has a light and thin design. This next-generation display system has additional advantages such as wide viewing angle, high contrast, and fast response. However, since organic system materials are susceptible to degradation from external moisture or oxygen, the light-emitting region must be effectively sealed.

[0004] In order to make an OLED display system lightweight and/or flexible, recent attempts have been made to develop a thin film encapsulation member that includes a stack of layers formed by laying down inorganic films, or organic films and inorganic films.

[0005] As an inorganic film will generally have a greater thickness, it may more effectively prevent penetration of external moisture or oxygen than an organic film. However, as the thickness of an inorganic film increases, stress also increases, thereby allowing the inorganic film to peel off. Once an encapsulation member is damaged or removed, the lifetime of the display is reduced.

[0006] For instance, U.S. patent application US 2012/0169229 A1 is directed to an OLED display including a plurality of thin film transistors (TFTs) in an active area of the display and an inorganic protective layer covering the TFTs, wherein the inorganic protective layer may be made of silicon nitride.

[0007] Furthermore, US 2005/0242720 A1 discloses a display device comprising a display unit with a plurality of thin film transistors thereon and an encapsulation layer that seals the display unit and has a stacked structure in

which inorganic barrier layers and organic buffer layers are alternately stacked.

SUMMARY OF CERTAIN INVENTIVE ASPECTS

[0008] The present invention provides an organic light-emitting display system which may improve a sealing force of a thin film encapsulation layer and a method of manufacturing the organic light-emitting display system.

[0009] According to an aspect of the present invention, there is provided an organic light-emitting display system as disclosed in claim 1, the display system including: a substrate; a display unit that defines an active area on the substrate and comprises a plurality of thin film transistors (TFTs); and an encapsulation layer that seals the display unit and has a stacked structure in which at least a first inorganic film, a first organic film, and a second inorganic film are sequentially stacked, wherein the TFTs includes an active layer, a gate electrode, a source electrode, a drain electrode, and an interlayer insulating film that is disposed between the gate electrode and the source electrode and between the gate electrode and the drain electrode, wherein the second inorganic film directly contacts the interlayer insulating film at points that are substantially outside the active area.

[0010] The second inorganic film and the interlayer insulating film are formed of the same material, wherein the film material is silicon nitride (SiNx).

[0011] The display unit further comprises an organic light-emitting device (OLED), wherein the OLED comprises: a pixel electrode that is connected to either one of the source electrode and the drain electrode; an intermediate layer that is formed on the pixel electrode and includes an organic light-emitting layer; and a counter electrode that is formed on the intermediate layer, wherein the first inorganic film is formed on the counter electrode.

[0012] The organic light-emitting display system may further include a protective layer that is formed between the counter electrode and the first inorganic film.

[0013] The protective layer may include a capping layer that covers the counter electrode and a shield layer that is formed on the capping layer. The shield layer may be formed of lithium fluoride (LiF) having a pin-hole structure.

[0014] The first inorganic film is formed of aluminum oxide (AlOx).

[0015] The encapsulation layer may further include a second organic film that is formed on the second inorganic film, and a third inorganic film that is formed on the second organic film, wherein the third inorganic film contacts a top surface of the second inorganic film at points that are substantially outside the active area.

[0016] The second inorganic film and the third inorganic film may be formed of the same material.

[0017] The coverage area of each of the second inorganic film and the third inorganic film is greater than the coverage area of the first inorganic film.

[0018] The interlayer insulating film and the second inorganic film are formed of the same material.

[0019] The organic light-emitting display system, wherein the protective layer comprises a capping layer that covers the counter electrode, and a shield layer that is formed on the capping layer, wherein the first inorganic film surrounds the protective layer.

[0020] The coverage area of the first inorganic film is greater than the coverage area of the first organic film.

[0021] The shield layer may be formed of lithium fluoride (LiF) having a pin-hole structure and the first inorganic film is formed of aluminum oxide (AlOx).

[0022] The encapsulation layer may further comprise a second organic film that is formed on the second inorganic film, and a third inorganic film that is formed on the second organic film, wherein the third inorganic film contacts a top surface of the second inorganic film outside the active area.

[0023] The second inorganic film and the third inorganic film are formed of the same material.

[0024] The film material is silicon nitride (SiNx).

[0025] The TFTs further comprises an active layer, a gate electrode, a source electrode, and a drain electrode, wherein the interlayer insulating film is disposed between the gate electrode and the source electrode and between the gate electrode and the drain electrode.

[0026] The organic light-emitting device comprises a pixel electrode that is connected to the TFTs, an intermediate layer that is disposed on the pixel electrode and comprises an organic light-emitting layer, and a counter electrode that is formed on the intermediate layer, wherein the capping layer covers the counter electrode.

[0027] According to another aspect of the present invention, there is provided a method of manufacturing an organic light-emitting display system according to claim 8, the method including: forming a display unit that defines an active area on a substrate; forming a protective layer on the display unit; forming a first inorganic film on the protective layer; forming a first organic film on the first inorganic film; and forming a second inorganic film to cover the first inorganic film and the first organic film, wherein the display unit comprises an interlayer insulating film that extends to points that are substantially outside of the active area, and the second inorganic film contacts a top surface of the interlayer insulating film outside the active area.

[0028] The forming of the protective layer comprises forming a capping layer on the display unit and forming a shield layer on the capping layer, wherein the shield layer is formed of lithium fluoride (LiF) having a pin-hole structure.

[0029] The first inorganic film is formed by using sputtering, and is formed of aluminum oxide (AlOx).

[0030] The method may further comprise: forming a second organic film on the second inorganic film; and forming a third inorganic film on the second organic film, wherein the second inorganic film and the third inorganic film are formed by using chemical vapor deposition

(CVD).

[0031] The third inorganic film contacts a top surface of the second inorganic film outside the active area, and the third inorganic film and the second inorganic film may be formed of the same material.

[0032] The interlayer insulating film and the second inorganic film are formed of the same material.

[0033] An organic light-emitting display system, comprising: a substrate; a display unit formed on the substrate comprising a central pixel portion having a plurality of pixels, each pixel comprising a thin film transistors (TFT) and an organic light emitting diode (OLED); and an encapsulation layer that seals the display unit and has a stacked structure in which at least a first inorganic film, a first organic film, and a second inorganic film are sequentially stacked, wherein the TFTs comprise a non-conductive layer, wherein the second inorganic film extends beyond the pixel portion and contact the non-conductive layer in a peripheral portion of the display.

[0034] The inorganic non-conductive layer is an interlayer insulating film.

BRIEF DESCRIPTION OF THE DRAWINGS

[0035] The above and other features and advantages of the disclosed technology will become more apparent by describing in detail exemplary embodiments thereof with reference to the attached drawings in which:

FIG. 1 is a plan view illustrating an organic light-emitting display system according to an embodiment of the disclosed technology;

FIG. 2 is a cross-sectional view taken along line I-I' of FIG. 1;

FIG. 3 is a cross-sectional view taken along line II-II' of FIG. 1;

FIG. 4 is an enlarged view illustrating a portion P of FIG. 3; and

FIGS. 5 through 7 are cross-sectional views for explaining a method of manufacturing the organic light-emitting display system of FIG. 1, according to an embodiment of the disclosed technology.

DETAILED DESCRIPTION OF CERTAIN INVENTIVE EMBODIMENTS

[0036] As used herein, the term "and/or" includes any and all combinations of one or more of the associated listed items. Expressions such as "at least one of," when preceding a list of elements, modify the entire list of elements and do not modify the individual elements of the list.

[0037] Accordingly, while exemplary embodiments are capable of various modifications and alternative forms, embodiments thereof are shown by way of example in the drawings and will herein be described in detail. It should be understood, however, that there is no intent to limit exemplary embodiments to the particular forms dis-

closed, but on the contrary, exemplary embodiments are to cover all modifications, equivalents, and alternatives falling within the scope of the invention. While describing the present invention, detailed descriptions about related well known functions or configurations that may blur the points of the present invention are omitted.

[0038] It will be understood that, although the terms first, second, etc. may be used herein to describe various elements, these elements should not be limited by these terms. These terms are only used to distinguish one element from another.

[0039] It will be understood that when an element or layer is referred to as being "formed on," another element or layer, it can be directly or indirectly formed on the other element or layer. That is, for example, intervening elements or layers may be present.

[0040] The present invention will now be described more fully with reference to the accompanying drawings, in which exemplary embodiments of the invention are shown. Like elements are denoted by like reference numerals in the drawings and a repeated explanation thereof will not be given. Thicknesses of layers and regions are enlarged for clarity in the drawings. Thicknesses of some layers and regions are exaggerated for convenience of explanation in the drawings.

[0041] FIG. 1 is a plan view illustrating an organic light-emitting display system 10 according to an embodiment. FIG. 2 is a cross-sectional view taken along line I-I' of FIG. 1. FIG. 3 is a cross-sectional view taken along line II-II' of FIG. 1. FIG. 4 is an enlarged view illustrating portion P of FIG. 3.

[0042] Referring to FIGS. 1 through 4, the organic light-emitting display system 10 includes a substrate 101, a display unit 200 that defines an active area AA on the substrate 101, and an encapsulation layer 300 that seals the display unit 200.

[0043] The substrate 101 can be rigid or flexible, and can be formed of plastic having high heat resistance and high durability such as polyimide, polyethylene terephthalate (PET), polycarbonate, polyethylene naphthalate, polyarylate (PAR), and polyetherimide. However, the present embodiment is not limited thereto, and the substrate 101 can be formed of any of other various materials such as metal and glass.

[0044] The display unit 200 defines the active area AA on the substrate 101, and includes a plurality of pixels, wherein each pixel has a thin film transistor (TFT) and an organic light-emitting device (OLED) which are electrically connected to each other. A pad unit 1 is typically disposed around the active area AA, and transmits an electrical signal from a power supply device (not shown) or a signal generating device (not shown) to the active area AA. While subsequent figures will explain various embodiments of a single TFT and OLED with respect to an individual pixel, it will be understood by a technologist who has skill in the relevant field that a matrix of pixels is formed in the active area at the same time using the layers and films that will be explained below. It will also

be understood that commercial products will typically employ several subpixels of different colors, such as red, green and blue to form a complete pixel, but such usage details are well-known and will not be further considered here. Furthermore, also not shown is any supporting circuitry that is used to complement the TFT and OLED to form a pixel or the circuitry required to drive data to the pixels, for example.

[0045] The display unit 200 with respect to a pixel will be explained in greater detail with reference to FIG. 3.

[0046] In this embodiment, a buffer layer 201 is formed on the substrate 101. The buffer layer 201 is formed over an entire surface of the substrate 101, that is, on and around the active area AA. The buffer layer 201 is used to prevent impurities from penetrating into the substrate 101 and planarize the substrate 101. It may be formed of any of various materials according to design needs.

[0047] For example, the buffer layer 201 may include an inorganic material such as silicon oxide, silicon nitride, silicon oxynitride, aluminum oxide, aluminum nitride, titanium oxide, or titanium nitride or an organic material such as polyimide, polyester, or acryl, and may have a stacked structure in which two or more of the materials are stacked.

[0048] With reference to Figure 2, the TFT is formed on the buffer layer 201 and includes an active layer 202, a gate electrode 204, a source electrode 206, and a drain electrode 207.

[0049] The active layer 202 may be formed of an inorganic semiconductor such as amorphous silicon or polysilicon, an organic semiconductor, or an oxide semiconductor, and includes a source region, a drain region, and a channel region.

[0050] A gate insulating film 203 is formed on the active layer 202. The gate insulating film 203 is formed to correspond to the entire surface of the substrate 101. That is, the gate insulating film 203 is formed on and around the active area AA of the substrate 101. The gate insulating film 203 for insulating the active layer 202 from the gate electrode 204 may be formed of an organic material or an inorganic material such as SiNx or SiO₂.

[0051] The gate electrode 204 is formed on the gate insulating film 203. The gate electrode 204 may be formed of gold (Au), silver (Ag), copper (Cu), nickel (Ni), platinum (Pt), palladium (Pd), aluminum (Al), or molybdenum (Mo), or an alloy such as Al:Nd or Mo:W, but embodiments are not limited thereto and gate electrode 204 may be formed of any of other various materials in consideration of design constraints.

[0052] An interlayer insulating film 205 is formed on the gate electrode 204. The interlayer insulating film 205 is generally formed to correspond to the entire surface of the substrate 101. That is, the interlayer insulating film 205 is formed on and around the active area AA.

[0053] The interlayer insulating film 205 that is disposed between the gate electrode 204 and the source electrode 206 and between the gate electrode 204 and the drain electrode 207 and insulates the gate electrode

204 from each of the source electrode 206 and the drain electrode 207 is formed of SiNx. The interlayer insulating film 205 is formed of SiNx, or has a two-layer structure including a SiNx layer and a SiO₂ layer. When the interlayer insulating film 205 has a two-layer structure, in order to improve the adhesive force between the interlayer insulating film 205 and the encapsulation layer, an upper layer is formed as a SiNx layer.

[0054] The source electrode 206 and the drain electrode 207 are formed on the interlayer insulating film 205. Furthermore, the interlayer insulating film 205 and the gate insulating film 203 are formed to expose the source region and the drain region of the active layer 202, and the source electrode 206 and the drain electrode 207 are formed to contact the exposed source region and the exposed drain region of the active layer 202.

[0055] Although the referenced TFT is shown as a top gate TFT in which the active layer 202, the gate electrode 204, and the source and drain electrodes 206 and 207 are sequentially stacked, embodiments are not limited thereto and the gate electrode 204 can be disposed under the active layer 202.

[0056] The TFT drives the OLED by being electrically connected to the OLED and is protected by being covered by a passivation layer 208.

[0057] The passivation layer 208 as disclosed includes an inorganic insulating film and/or an organic insulating film. The inorganic insulating film may be formed of SiO₂, SiNx, SiON, Al₂O₃, TiO₂, Ta₂O₅, HfO₂, ZrO₂, BST, or PZT, and the organic insulating film may be formed of a general polymer such as polymethyl methacrylate (PMMA) or polystyrene (PS), a polymer derivative having a phenol group, an acryl-based polymer, an imide-based polymer, an aryether-based polymer, an amide-based polymer, a fluorine-based polymer, a p-xylene-based polymer, a vinyl alcohol-based polymer, or a blend thereof. Also, the disclosed passivation layer 208 has a stacked structure including an inorganic insulating film and an organic insulating film.

[0058] The light-emissive device such as OLED is generally formed on the passivation layer 208, and it includes a pixel electrode 211, an intermediate layer 214, and a counter electrode 215.

[0059] The pixel electrode 211 is formed on the passivation layer 208. Furthermore, the passivation layer 208 may be formed to expose a predetermined portion of the drain electrode without covering the entire surface of the drain electrode 207, and the pixel electrode 211 may be formed to be connected to the exposed portion of the drain electrode 207.

[0060] The pixel electrode 211 may be a reflective electrode, and may include a reflective film formed of silver (Ag), magnesium (Mg), aluminum (Al), platinum (Pt), palladium (Pd), gold (Au), nickel (Ni), neodymium (Nd), iridium (Ir), chromium (Cr), or a compound thereof, and a transparent or semi-transparent electrode layer formed on the reflective film. The transparent or semi-transparent electrode layer may include at least one selected from

the group consisting of indium tin oxide (ITO), indium zinc oxide (IZO), zinc oxide (ZnO), indium oxide (In₂O₃), indium gallium oxide (IGO), and aluminum zinc oxide (AZO).

[0061] The counter electrode 215 that faces the pixel electrode 211 may be a transparent or semi-transparent electrode, and may include a metal thin film having a low work function formed of lithium (Li), calcium (Ca), lithium fluoride (LiF)/Ca, LiF/Al, Al, Ag, Mg, or a compound thereof. Also, an auxiliary electrode layer or a bus electrode formed of a transparent electrode-forming material such as ITO, IZO, ZnO, or In₂O₃ may be further formed on the metal thin film.

[0062] Accordingly, the counter electrode 215 transmits therethrough light emitted from an organic light-emitting layer included in the intermediate layer 214. That is, light emitted from the organic light-emitting layer will be directly transmitted to the counter electrode 215, or will be reflected by the pixel electrode 211 including a reflective electrode and then transmitted to the counter electrode 215.

[0063] However, the organic light-emitting display system 10 is not limited to a top emission organic light-emitting display system, and may be a bottom emission organic light-emitting display system in which light emitted from the organic light-emitting layer is transmitted to the substrate 101. In this case, the pixel electrode 211 may be a transparent or semi-transparent electrode, and the counter electrode 215 may be a reflective electrode. Also, the organic light-emitting display system 10 may be a dual-sided emission organic light-emitting display system in which light is transmitted to both a top surface and a bottom surface.

[0064] A pixel-defining film 213 formed of an insulating material is formed on the pixel electrode 211. The pixel-defining film 213 is processed to expose a predetermined portion of the pixel electrode 211, and the intermediate layer 214, including the organic light-emitting layer, is formed on the exposed portion of the pixel electrode 211.

[0065] The organic light-emitting layer may be formed of either a low molecular weight organic material or a high molecular weight organic material. The intermediate layer 214 may selectively further include a functional layer such as a hole transport layer (HTL), a hole injection layer (HIL), an electron transport layer (ETL), or an electron injection layer (EIL) in addition to the organic light-emitting layer.

[0066] The encapsulation layer 300 is formed on the counter electrode 215. In the depicted embodiment, the encapsulation layer 300 includes at least a first inorganic film 301, a first organic film 302, and a second inorganic film 303. Also, as shown in Figure 4, a protective layer 220 may be further formed between the encapsulation layer 300 and the display unit 200.

[0067] The protective layer 220 may include a capping layer 222 that covers the counter electrode 215, and a shield layer 224 that is disposed on the capping layer 222.

[0068] The capping layer 222 may be formed of an

organic material such as a-NPD, NPB, TPD, m-MTDATA, Alq₃, or CuPc. The capping layer 222 is used to enhance light transmission as well as protect the OLED.

[0069] The shield layer 224 may be formed of an inorganic material such as LiF, MgF₂, or CaF₂. The shield layer 224 is used to prevent plasma used in forming the first inorganic film 310 from penetrating into the OLED and damaging the intermediate layer 214 and the counter electrode 215. The shield layer 224 may be formed of LiF having a pin-hole structure.

[0070] The first inorganic film 301 is formed on the protective layer 220. The first inorganic film 310 is formed of aluminum oxide (AlOx). The first inorganic film 301 may be formed by using sputtering to a thickness of about 500 Å. The first inorganic film 301 deposited on the shield layer 224 is grown according to a crystal structure of the shield layer 224. That is, fine cracks exist on the entire surface of the first inorganic film 301 formed on the shield layer 224.

[0071] The first organic film 302 formed on the first inorganic film 301 may include a high molecular weight organic compound. Outgassing in which gas is released can occur in the high molecular weight organic compound. The gas can penetrate into the OLED. In this case, when the first inorganic film 301 is cracked by particles or the like, the gas generated in the organic compound can concentrate on the cracks, thereby oxidizing the counter electrode 215 of the OLED and resulting in unintended dark spots.

[0072] However, according to various embodiments, since the fine cracks exist on the entire surface of the first inorganic film 301, even when gas is released from the first organic film 302, the gas may not be concentrated on a single point. That is, since gas generated in the first organic film 302 is widely distributed by the fine cracks existing on the entire surface (on average), the counter electrode 215 will generally not be oxidized, and thus, dark spots can be minimized or avoided.

[0073] The first organic film 302 can be formed on the first inorganic film 301 to have a predetermined thickness, for example, a thickness of about 30000 Å so as to planarize a stepped portion (see OLED label in Figure 3) formed due to the OLED processing including formation of the pixel-defining film 213. The first organic film 302 may be formed of any one of epoxy, acrylate, and urethane acrylate. Typically, the coverage area of the first organic film 302 will be less than the coverage area of the first inorganic film 301.

[0074] The second inorganic film 303 is formed to surround the first inorganic film 301 and the first organic film 302. That is, since the entire surface of the first organic film 302 is surrounded by the first inorganic film 301 and the second inorganic film 303, penetration of external moisture or oxygen into the active area of the display may be effectively prevented.

[0075] The second inorganic film 303 is formed of SiNx, and may be formed by using chemical vapor deposition (CVD) to a thickness of about 10000 Å. Accordingly, even

when particles exist on the first organic film 302, a raised portion formed due to particles being introduced during the manufacturing process will be covered. Also, since the second inorganic film 303 is formed by using CVD that does not use plasma, the first organic film 302 will not be damaged when the second inorganic film 303 is formed, and thus, outgassing will be prevented.

[0076] The second inorganic film 303 is formed to cover a larger area than the first inorganic film 301, and directly contacts the interlayer insulating film 205 at points that are substantially outside the active area AA. Also, the second inorganic film 303 is formed of the same material as the material of the interlayer insulating film 205. That is, since the second inorganic film 303 is formed of SiNx, and the interlayer insulating film 205 is formed of SiNx or when the interlayer insulating film 205 has a two-layer structure, an upper layer is a SiNx layer, an adhesive force between the second inorganic film 303 and the interlayer insulating film 205 will be enhanced. Accordingly, in various embodiments, as the second inorganic film 303 is formed to a thickness sufficient to cover undesired particulate matter, even when stress on the film increases, the second inorganic film 303 is prevented from being peeled off to large extent, and thus, penetration of unwanted external moisture or oxygen is reduced or avoided.

[0077] A second inorganic film 304 and a third inorganic film 305 may be formed on the second inorganic film 303. Although not shown in FIGS. 1 through 4, in other embodiments, a fourth inorganic film (not shown) formed of AlOx may be further formed on an outer surface of the encapsulation layer 300.

[0078] The second organic film 304 may be formed of any one of epoxy, acrylate, and urethane acrylate, and may be formed to a thickness of about 10000 Å. The second organic film 304 is used to reduce stress on the first inorganic film 301 and planarize particles, if any.

[0079] The third inorganic film 305 covers the second organic film 304. The third inorganic film 305 has a thickness of about 10000 Å, and contacts a top surface of the second inorganic film 303 at points that are substantially outside the active area AA.

[0080] The third inorganic film 305 may be formed of the same material as the material of the second inorganic film 303. For example, the third inorganic film 305 may be formed of SiNx. Accordingly, the adhesive force between the third inorganic film 305 and the second inorganic film 303 should increase, thereby effectively further preventing penetration of external moisture or oxygen.

[0081] The encapsulation layer 300 may further include a plurality of additional inorganic films and organic films which are alternately stacked, and the number of the inorganic films and organic layers which are stacked is not limited.

[0082] Also, a protective film (not shown) is attached to a top surface of the encapsulation layer 300. When the protective film has a strong adhesive force, when the protective film is removed, the encapsulation layer 300

may be peeled off as well. In order to solve this problem, a fourth inorganic film (not shown) formed of AlOx having a weak adhesive force with the protective film may be further formed.

[0083] FIGS. 5 through 7 are cross-sectional views for explaining a method of manufacturing the organic light-emitting display system 10 of FIG. 1. The display unit 200 is the same as that described with reference to FIG. 3, and thus part of a structure of the display unit 200 is not shown in FIGS. 5 through 7.

[0084] A method of manufacturing the organic light-emitting display system 10 will be explained with reference to FIGS. 5 through 7 along with FIG. 4.

[0085] Referring to FIG. 5, the display unit 200 that defines the active area AA is formed on the substrate 101. Since the display unit 200 may incorporate a pixel structure as shown in FIG. 3 and may be made of any of various well-known organic light-emitting display designs, a method of manufacturing the display unit 200 will not be explained. The display unit 200 includes the buffer layer 201, the gate insulating film 203, and the interlayer insulating film 205 which extend to locations that are substantially outside the active area AA. The interlayer insulating film 205 which is disposed between the gate electrode 204 (see FIG. 3) and the source electrode 206 (see FIG. 3) and between the gate electrode 204 (see FIG. 3) and the drain electrode 207 (see FIG. 3) and insulates the gate electrode 204 from each of the source electrode 206 and the drain electrode 207 is formed of SiNx. The interlayer insulating film 205 is formed of SiNx, or is formed to have a two-layer structure including a SiNx layer and a SiO₂ layer. When the interlayer insulating film 205 has a two-layer structure, an upper layer is a SiNx layer in order to improve the adhesive force between the interlayer insulating film 205 and the second inorganic film 303.

[0086] Referring to FIG. 6, the protective layer 220 and the first inorganic film 301 are formed on the display unit 200.

[0087] The protective layer 220 includes the capping layer 222 formed of an organic material such as a-NPD, NPB, TPD, m-MTDATA, Alq₃, or CuPc, and the shield layer 224 formed of LiF. The first inorganic film 301 is formed of AlOx. Also, the first inorganic film 301 may be formed by using sputtering to a thickness of about 500 Å.

[0088] Since the lithium fluoride (LiF) has a pin-hole structure and the first inorganic layer 301 deposited on the shield layer 224 is grown according to a crystal structure of the shield layer 224, fine cracks exist on an entire surface of the first inorganic film 301. Accordingly, even when a gas is generated in the first organic film 302 (see FIG. 7) formed on the first inorganic film 301, the gas will generally be widely distributed by the fine cracks existing on the entire surface of the first inorganic film 301 (on average), and may be prevented from concentrating on a single point. Accordingly, the counter electrode 215 may be prevented from being oxidized and dark spots may be avoided.

[0089] Referring to FIG. 7, the first organic film 302, the second inorganic film 303, the second organic film 304, and the third inorganic film 305 are sequentially formed.

[0090] The first organic film 302 may be formed to a predetermined thickness, for example, a thickness of about 30000 Å, great enough to planarize a stepped portion formed due to the pixel-defining film 213 (see FIG. 3). The first organic film 302 may be formed of any one of epoxy, acrylate, and urethane acrylate. In order for the covered area of the first organic film 302 to be less than the covered area of the first inorganic film 301, a mask having a smaller opening may be used to form the first organic film 302.

[0091] The second inorganic film 303 is formed to surround the first inorganic film 301 and the first organic film 302. That is, since an entire surface of the first organic film 302 is surrounded by the first inorganic film 301 and the second inorganic film 303, penetration of external moisture or oxygen will be reduced or prevented.

[0092] The second inorganic film 303 is formed of SiNx, and may be formed by using CVD to a thickness of about 10000 Å. Accordingly, even when particles exist on the first organic film 302, a raised portion formed due to the particles will be covered. Also, since the second inorganic film 303 is formed by using CVD that does not use plasma, the first organic film 302 may be prevented from being damaged when the second inorganic film 303 is formed, thereby preventing outgassing in which a gas is generated in the first organic film 302.

[0093] The second inorganic film 303 is formed to be larger in area than the first inorganic film 301, and directly contacts the interlayer insulating film 205 at points that are substantially outside the active area AA. Also, the second inorganic film 303 is formed of the same material as a material of the interlayer insulating film 205. For example, since the second inorganic film 303 is formed of SiNx, and the interlayer insulating film 205 is formed of SiNx or when the interlayer insulating film 205 has a two-layer structure, an upper layer is a SiNx layer, the adhesive force between the second inorganic film 303 and the interlayer insulating film 205 may be improved. Accordingly, as the second inorganic film 303 is formed to a thickness that is sufficient to cover undesired particulate matter, even when stress on the film is increased, the second inorganic film 303 may be prevented from being peeled off and thus penetration of external moisture or oxygen will be reduced or prevented.

[0094] The second organic film 304 may include any one of epoxy, acrylate, and urethane acrylate, and may be formed to a thickness of about 10000 Å. The second organic film 304 reduces stress on the first organic film 301, and planarizes particles, if any.

[0095] The third inorganic film 305 covers the second organic film 304. The third inorganic film 305 may have a thickness of about 10000 Å, and may be formed by using CVD, thereby preventing damage to the second organic film 304.

[0096] Also, the third inorganic film 305 may contact a top surface of the second inorganic film 303 outside the active area AA, and the third inorganic film 305 may be formed of the same material as a material of the second inorganic film 303. For example, the third inorganic film 305 may be formed of SiNx. Accordingly, the adhesive force between the third inorganic film 305 and the second inorganic film 303 will be enhanced, thereby effectively preventing penetration of external moisture or oxygen.

[0097] The encapsulation layer 300 may further include a plurality of additional inorganic films and organic films which are alternately stacked. The number of the inorganic films and organic films which are stacked is not limited.

[0098] A flexible display system according to the present invention is not limited to the structures and methods of the disclosed embodiments, and the embodiments may be modified by selectively combining all or some elements of other embodiments.

[0099] While the inventive concept has been particularly shown and described with reference to exemplary embodiments thereof, they are provided for the purposes of illustration and it will be understood by those of ordinary skill in the art that various modifications and equivalent embodiments can be made from the inventive concept. Accordingly, the technical scope of the inventive concept is defined by the appended claims.

Claims

1. An organic light-emitting display system, comprising:

a substrate (101);
a display unit (200) that defines an active area (AA) on the substrate (101) and comprises a plurality of thin film transistors (TFTs); and
an encapsulation layer (300) that seals the display unit (200) and comprises a second inorganic film (303);
wherein the TFTs comprise

an active layer (202), a gate electrode (204), a source electrode (206) and a drain electrode (207), wherein the active layer (202), the gate electrode (204), and the source and drain electrodes (206, 207) are sequentially stacked, and
an interlayer insulating film (205) disposed between the gate electrode (204) and the source electrode (206) and between the gate electrode (204) and the drain electrode (207), the interlayer insulating film (205) being formed to correspond to the entire surface of the substrate (101),

wherein the second inorganic film (303) directly contacts the interlayer insulating film (205) of

the TFTs outside the active area, and
characterized in that the encapsulation layer (300) has a stacked structure in which at least a first inorganic film (301), a first organic film (302), and the second inorganic film (303) are sequentially stacked, wherein the first inorganic film (301) is the innermost film of the encapsulation layer (300) which is closest to the display unit (200), the first organic film (302) being formed on a surface of the first inorganic film (301) facing away from the display unit (200) and the second inorganic film (303) being formed on a surface of the first organic film (302) opposed to the surface facing the first inorganic film (301), wherein the second inorganic film (302) covers a larger area than the first inorganic film (301) and the first organic film (302), the first inorganic film is formed of aluminum oxide (AlOx),
the second inorganic film (303) is formed of silicon nitride (SiNx), and
the interlayer insulating film (205) is also formed of silicon nitride (SiNx) or, when the interlayer insulating film (205) has a two-layer structure, an upper layer of the interlayer insulating film (205) is formed of silicon nitride (SiNx), wherein the upper layer is the layer contacting the second inorganic film (303).

2. The organic light-emitting display system of claim 1, wherein the coverage area of the second inorganic film (303) is greater than the coverage area of each of the first inorganic film (301) and the first organic film (302) and wherein the coverage area of the first inorganic film (301) is greater than the coverage area of the first organic film (302).

3. The organic light-emitting display system of one of the preceding claims, wherein the display unit further comprises a plurality of organic light-emitting devices (OLEDs), each of the OLEDs being electrically connected to a respective one of the TFTs, wherein each of the OLEDs comprises:

a pixel electrode (211) that is connected to either one of the source electrode (206) and the drain electrode (207);
an intermediate layer (214) that is formed on the pixel electrode (211) and comprises an organic light-emitting layer; and
a counter electrode (215) that is formed on the intermediate layer (214),
wherein the first inorganic film (301) is formed on the counter electrode (215).

4. The organic light-emitting display system of claim 3, further comprising a protective layer (220) that is formed between the counter electrode (215) and the

first inorganic film (301).

5. The organic light-emitting display system of claim 4, wherein the protective layer (220) comprises a capping layer (222) that covers the counter electrode (215) and a shield layer (224) that is formed on the capping layer (222) wherein the first inorganic film (301) completely covers the protective layer (220), and wherein the shield layer (224) is formed of lithium fluoride (LiF) having a pin-hole structure.

6. The organic light-emitting display system of one of the preceding claims, wherein the encapsulation layer further comprises:

a second organic film (304) that is formed on the second inorganic film (303), and
a third inorganic film (305) that is formed on the second organic film (304),
wherein the third inorganic film (305) contacts a top surface of the second inorganic film (303) in a region outside the active area (AA), and
wherein the coverage area of each of the second inorganic film (303) and the third inorganic film (305) is greater than the coverage area of the first inorganic film (301).

7. The organic light-emitting display system of claim 6, wherein the second inorganic film (303) and the third inorganic film (305) are formed of the same material.

8. A method of manufacturing an organic light-emitting display system according to one of the preceding claims, the method comprising:

forming a display unit (200) that defines an active area (AA) on a substrate (101);
forming a first inorganic film (301) on the display unit (200);
forming a first organic film (302) on the first inorganic film (301); and
forming a second inorganic film (303) to cover the first inorganic film (301) and the first organic film (302), wherein the first inorganic film is formed of aluminum oxide (AlOx), the second inorganic film (303) is formed of silicon nitride (SiNx),
wherein the display unit (200) comprises an interlayer insulating film (205) that extends to a region outside of the active area (AA), and the second inorganic film (303) contacts a top surface of the interlayer insulating film (205) outside the active area, and wherein at least an upper layer of the interlayer insulating film (205) is formed of silicon nitride (SiNx).

9. The method of claim 8, further comprising forming a protective layer (220) on the display unit

(200),

wherein the forming of the protective layer comprises forming a capping layer (222) on the display unit (200) and forming a shield layer (224) on the capping layer (222).

10. The method of one of claims 8 and 9, wherein the first inorganic film (301) is formed by using sputtering.

11. The method of one of claims 8 to 10, further comprising:

forming a second organic film (304) on the second inorganic film (303); and
forming a third inorganic film (305) on the second organic film (304),
wherein the second inorganic film (303) and the third inorganic film (305) are formed by using chemical vapor deposition (CVD).

Patentansprüche

1. Organisches lichtemittierendes Anzeigesystem, umfassend:

ein Substrat (101);
eine Anzeigeeinheit (200), die eine aktive Fläche (AA) auf dem Substrat (101) definiert und eine Vielzahl von Dünnschichttransistoren (TFTs) umfasst; und eine Verkapselungsschicht (300), die die Anzeigeeinheit (200) versiegelt und einen zweiten anorganischen Film (303) umfasst,
wobei die TFTs umfassen

eine aktive Schicht (202), eine Gate-Elektrode (204), eine Source-Elektrode (206) und eine Drain-Elektrode (207), wobei die aktive Schicht (202), die Gate-Elektrode (204) und die Source- und Drain-Elektroden (206, 207) nacheinander gestapelt sind, und
einen Zwischenschicht-Isolierfilm (205), der zwischen der Gate-Elektrode (204) und der Source-Elektrode (206) und zwischen der Gate-Elektrode (204) und der Drain-Elektrode (207) angeordnet ist, wobei der Zwischenschicht-Isolierfilm (205) gebildet ist, um der gesamten Oberfläche des Substrats (101) zu entsprechen,

wobei der zweite anorganische Film (303) den Zwischenschicht-Isolierfilm (205) der TFTs außerhalb des aktiven Bereichs direkt kontaktiert, und

dadurch gekennzeichnet, dass

- die Verkapselungsschicht (300) eine Stapelstruktur aufweist, in der mindestens ein erster anorganischer Film (301), ein erster organischer Film (302) und den zweiter anorganischer Film (303) nacheinander gestapelt sind, wobei der erste organische Film (301) der innerste Film der Verkapselungsschicht (300) ist, der der Anzeigeeinheit (200) am nächsten liegt, wobei der erste organische Film (302) auf einer Oberfläche des ersten anorganischen Films (301) gebildet ist, die von der Anzeigeeinheit (200) abgewandt ist, und der zweite anorganische Film (303) auf einer Oberfläche des ersten organischen Films (302) gebildet ist, die der Oberfläche gegenüberliegt, die dem ersten anorganischen Film (301) zugewandt ist, worin der zweite anorganische Film (302) einen größeren Bereich abdeckt als der erste anorganische Film (301) und der erste organische Film (302), der erste anorganische Film aus Aluminiumoxid (AlOx) gebildet ist, der zweite anorganische Film (303) aus Siliziumnitrid (SiNx) gebildet ist, und der Zwischenschicht-Isolierfilm (205) ebenfalls aus Siliziumnitrid (SiNx) gebildet ist oder, wenn der Zwischenschicht-Isolierfilm (205) einen zweischichtigen Aufbau aufweist, eine obere Schicht des Zwischenschicht-Isolierfilms (205) aus Siliziumnitrid (SiNx) gebildet ist, worin die obere Schicht die Schicht ist, die den zweiten anorganischen Film (303) berührt.
2. Organisches lichtemittierendes Anzeigesystem nach Anspruch 1, wobei der Abdeckungsbereich des zweiten anorganischen Films (303) größer ist als der Abdeckungsbereich jedes der ersten anorganischen Filme (301) und des ersten organischen Films (302) und wobei der Abdeckungsbereich des ersten anorganischen Films (301) größer ist als der Abdeckungsbereich des ersten organischen Films (302).
 3. Organisches lichtemittierendes Anzeigesystem nach einem der vorstehenden Ansprüche, worin die Anzeigeeinheit ferner eine Vielzahl von organischen lichtemittierenden Vorrichtungen (OLEDs) umfasst, wobei jedes der OLEDs elektrisch mit einem der TFTs verbunden ist, worin jedes der OLEDs umfasst:
 - eine Pixelelektrode (211), die mit einer der beiden Quellenelektroden (206) und der Drain-Elektrode (207) verbunden ist;
 - eine Zwischenschicht (214), die auf der Pixelelektrode (211) ausgebildet ist und eine organische lichtemittierende Schicht umfasst; und
 - eine Gegenelektrode (215), die auf der Zwischenschicht (214) ausgebildet ist, wobei der erste anorganische Film (301) auf der Gegenelektrode (215) gebildet ist.
 4. Organisches lichtemittierendes Anzeigesystem nach Anspruch 3, ferner umfassend eine Schutzschicht (220), die zwischen der Gegenelektrode (215) und dem ersten anorganischen Film (301) gebildet ist.
 5. Organisches lichtemittierendes Anzeigesystem nach Anspruch 4, wobei die Schutzschicht (220) eine Deckschicht (222), die die Gegenelektrode (215) bedeckt, und eine Abschirmschicht (224) umfasst, die auf der Deckschicht (222) ausgebildet ist, wobei der erste anorganische Film (301) die Schutzschicht (220) vollständig bedeckt, und wobei die Abschirmschicht (224) aus Lithiumfluorid (LiF) mit einer Stiftlochstruktur gebildet ist.
 6. Organisches lichtemittierendes Anzeigesystem nach einem der vorhergehenden Ansprüche, worin die Verkapselungsschicht ferner umfasst:
 - einen zweiten organischen Film (304), der auf dem zweiten anorganischen Film (303) gebildet ist, und
 - einen dritten anorganischen Film (305), der auf dem zweiten organischen Film (304) gebildet ist, wobei der dritte anorganische Film (305) eine Oberseite des zweiten anorganischen Films (303) in einem Bereich außerhalb des aktiven Bereichs (AA) berührt, und
 - wobei der Abdeckungsbereich jedes der zweiten anorganischen Filme (303) und der dritten anorganischen Filme (305) größer ist als der Abdeckungsbereich der ersten anorganischen Filme (301).
 7. Organisches lichtemittierendes Anzeigesystem nach Anspruch 6, worin der zweite anorganische Film (303) und der dritte anorganische Film (305) aus dem gleichen Material gebildet sind.
 8. Verfahren zur Herstellung eines organischen lichtemittierenden Anzeigesystems gemäß einem der vorhergehenden Ansprüche, wobei das Verfahren umfasst:
 - Bilden einer Anzeigeeinheit (200), die eine aktive Fläche (AA) auf einem Substrat (101) definiert;
 - Bilden eines ersten anorganischen Films (301) auf der Anzeigeeinheit (200);
 - Bilden eines ersten organischen Films (302) auf dem ersten anorganischen Film (301); und
 - Bilden eines zweiten anorganischen Films (303) zum Abdecken des ersten anorganischen Films (301) und des ersten organischen Films (302), wobei der erste anorganische Film aus Aluminiumoxid (AlOx) gebildet ist, der zweite anorganische Film (303) aus Siliziumnitrid (SiNx) ge-

bildet ist,
 wobei die Anzeigeeinheit (200) einen Zwischen-
 schicht-Isolierfilm (205) umfasst, der sich zu ei-
 nem Bereich außerhalb des aktiven Bereichs
 (AA) erstreckt, und der zweite anorganische
 Film (303) eine obere Oberfläche des Zwischen-
 schicht-Isolierfilms (205) außerhalb des aktiven
 Bereichs kontaktiert, und wobei mindestens ei-
 ne obere Schicht des Zwischenschicht-Isolier-
 films (205) aus Siliziumnitrid (SiNx) gebildet ist.

9. Verfahren nach Anspruch 8, ferner umfassend
 Bilden einer Schutzschicht (220) auf der Anzeigeeinheit (200),
 wobei das Bilden der Schutzschicht das Bilden einer
 Deckschicht (222) auf der Anzeigeeinheit (200) und
 das Bilden einer Abschirmschicht (224) auf der
 Deckschicht (222) umfasst.
10. Verfahren nach einem der Ansprüche 8 und 9, worin
 der erste anorganische Film (301) durch Sputtern
 gebildet wird.
11. Verfahren nach einem der Ansprüche 8 bis 10, ferner
 umfassend:
 Bilden eines zweiten organischen Films (304)
 auf dem zweiten anorganischen Film (303); und
 Bilden eines dritten anorganischen Films (305)
 auf dem zweiten organischen Film (304),
 wobei der zweite anorganische Film (303) und
 der dritte anorganische Film (305) unter Ver-
 wendung der chemischen Dampfabcheidung
 (CVD) gebildet werden.

Revendications

1. Système d'affichage luminescent organique
 comprenant :
 un substrat (101) ;
 une unité d'affichage (200) qui définit une zone
 active (AA) sur le substrat (101) et qui comprend
 une pluralité de transistors à couches minces
 (TFT) ; et
 une couche d'encapsulation (300) qui scelle
 l'unité d'affichage (200) et comprend un deuxième
 film inorganique (303) ;
 dans lequel les TFT comprennent
 une couche active (202), une électrode de grille
 (204), une électrode de source (206) et une élec-
 trode de drain (207), parmi lesquelles la couche
 active (202), l'électrode de grille (204) et les
 électrodes de source et de drain (206, 207) sont
 empilées en séquence, et
 un film isolant inter-couche (205) disposé entre
 l'électrode de grille (204) et l'électrode de source

(206) et entre l'électrode de grille (204) et l'élec-
 trode de drain (207), le film isolant inter-couche
 (205) étant formé de manière à correspondre à
 toute la surface du substrat (101),
 dans lequel le deuxième film inorganique (303)
 est en contact direct avec le film isolant inter-
 couche (205) des TFT à l'extérieur de la zone
 active, et

caractérisé en ce que

la couche d'encapsulation (300) a une structure
 empilée dans laquelle au moins un premier film
 inorganique (301), un premier film organique
 (302) et le deuxième film inorganique (303) sont
 empilés en séquence, dans lequel le premier
 film inorganique (301) est le film le plus intérieur
 de la couche d'encapsulation (300) qui est la
 plus proche de l'unité d'affichage (200), le pre-
 mier film organique (302) étant formé sur une
 surface du premier film inorganique (301) oppo-
 sée à l'unité d'affichage (200) et le deuxième
 film inorganique (303) étant formé sur une sur-
 face du premier film organique (302) opposée à
 la surface faisant face au premier film inorgani-
 que (301), dans lequel le deuxième film inorga-
 nique (302) couvre une plus grande zone que
 le premier film inorganique (301) et le premier
 film organique (302),
 le premier film inorganique est formé d'oxyde
 d'aluminium (AlOx) ,
 le deuxième film inorganique (303) est formé de
 nitrure de silicium (SiNx), et
 le film isolant inter-couche (205) est aussi formé
 de nitrure de silicium (SiNx) ou, quand le film
 isolant inter-couche (205) a une structure bicou-
 che, la couche supérieure du film isolant inter-
 couche (205) est formée de nitrure de silicium
 (SiNx), laquelle couche supérieure est la couche
 en contact avec le deuxième film inorganique
 (303).

2. Système d'affichage luminescent organique selon la
 revendication 1, dans lequel la zone de couverture
 du deuxième film inorganique (303) est supérieure
 à la zone de couverture de chacun parmi le premier
 film inorganique (301) et le premier film organique
 (302), et dans lequel la zone de couverture du pre-
 mier film inorganique (301) est supérieure à la zone
 de couverture du premier film organique (302).
3. Système d'affichage luminescent organique selon
 l'une des revendications précédentes, dans lequel
 l'unité d'affichage comprend en outre une pluralité
 de dispositifs luminescents organiques (OLED),
 chacun des OLED étant connecté électriquement à
 l'un respectif des TFT, dans lequel chacun des
 OLED comprend :

une électrode de pixel (211) qui est connectée

- à l'une ou l'autre parmi l'électrode de source (206) et l'électrode de drain (207) ;
une couche intermédiaire (214) qui est formée sur l'électrode de pixel (211) et qui comprend une couche luminescente organique ; et
une contre-électrode (215) qui est formée sur la couche intermédiaire (214),
dans lequel le premier film inorganique (301) est formé sur la contre-électrode (215).
4. Système d'affichage luminescent organique selon la revendication 3, comprenant en outre une couche protectrice (220) qui est formée entre la contre-électrode (215) et le premier film inorganique (301).
5. Système d'affichage luminescent organique selon la revendication 4, dans lequel la couche protectrice (220) comprend une couche de recouvrement (222) qui couvre la contre-électrode (215) et une couche de protection (224) qui est formée sur la couche de recouvrement (222), dans lequel le premier film inorganique (301) couvre complètement la couche de protection (220), et dans lequel la couche de protection (224) est formée de fluorure de lithium (LiF) ayant une structure en piqures d'épingle.
6. Système d'affichage luminescent organique selon l'une des revendications précédentes, dans lequel la couche d'encapsulation comprend en outre :
- un deuxième film organique (304) qui est formé sur le deuxième film inorganique (303), et
un troisième film inorganique (305) qui est formé sur le deuxième film organique (304),
dans lequel le troisième film inorganique (305) est en contact avec une surface supérieure du deuxième film inorganique (303) dans une région à l'extérieur de la zone active (AA), et
dans lequel la zone de couverture de chacun parmi le deuxième film inorganique (303) et le troisième film inorganique (305) est supérieure à la zone de couverture du premier film inorganique (301).
7. Système d'affichage luminescent organique selon la revendication 6, dans lequel le deuxième film inorganique (303) et le troisième film inorganique (305) sont formés du même matériau.
8. Procédé de fabrication d'un système d'affichage luminescent organique selon l'une des revendications précédentes, le procédé comprenant les opérations consistant à :
- former une unité d'affichage (200) qui définit une zone active (AA) sur un substrat (101) ;
former un premier film inorganique (301) sur l'unité d'affichage (200) ;
former un premier film organique (302) sur le premier film inorganique (301) ; et
former un deuxième film inorganique (303) pour couvrir le premier film inorganique (301) et le premier film organique (302),
dans lequel le premier film inorganique est formé d'oxyde d'aluminium (AlOx), le deuxième film inorganique (303) est formé de nitrure de silicium (SiNx),
dans lequel l'unité d'affichage (200) comprend un film isolant inter-couche (205) qui s'étend jusqu'à une région à l'extérieur de la zone active (AA), et le deuxième film inorganique (303) est en contact avec une surface supérieure du film isolant inter-couche (205) à l'extérieur de la zone active, et dans lequel au moins une couche supérieure du film isolant inter-couche (205) est formée de nitrure de silicium (SiNx).
9. Procédé selon la revendication 8, comprenant en outre l'opération consistant à former une couche protectrice (220) sur l'unité d'affichage (200), dans lequel la formation de la couche protectrice comprend la formation d'une couche de recouvrement (222) sur l'unité d'affichage (200) et la formation d'une couche de protection (224) sur la couche de recouvrement (222).
10. Procédé selon l'une des revendications 8 et 9, dans lequel le premier film inorganique (301) est formé par utilisation d'une pulvérisation cathodique.
11. Procédé selon l'une des revendications 8 à 10, comprenant en outre les opérations consistant à :
- former un deuxième film organique (304) sur le deuxième film inorganique (303) ; et
former un troisième film inorganique (305) sur le deuxième film organique (304),
dans lequel le deuxième film inorganique (303) et le troisième film inorganique (305) sont formés par utilisation d'un dépôt chimique en phase vapeur (CVD).

FIG. 1

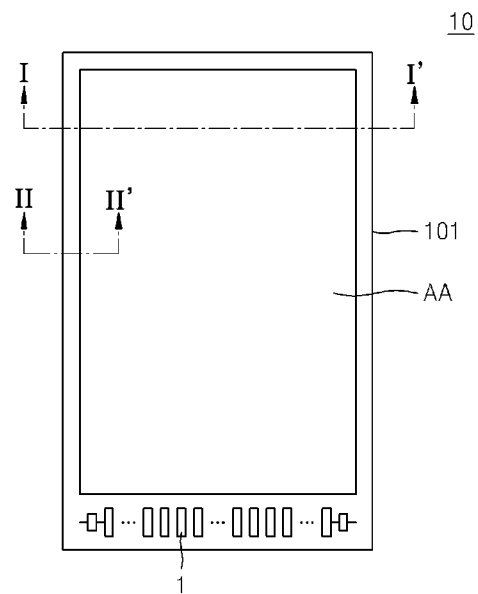


FIG. 2

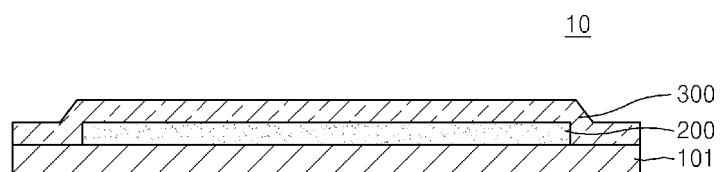


FIG. 3

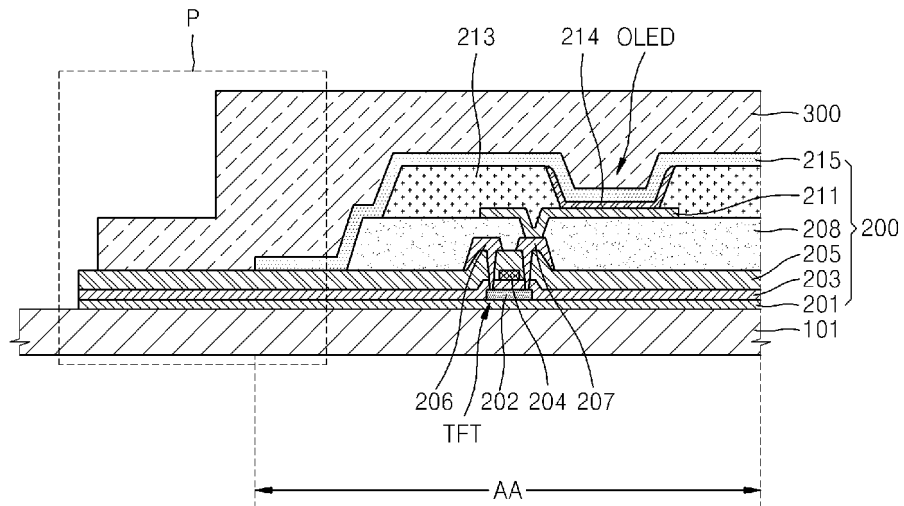


FIG. 4

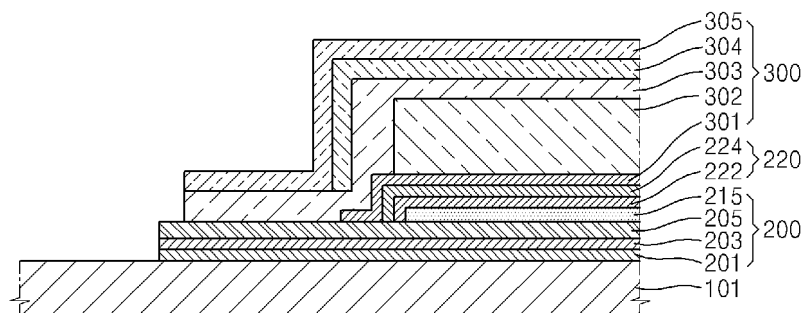


FIG. 5

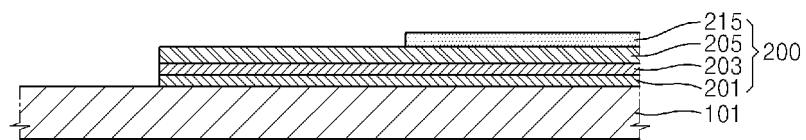


FIG. 6

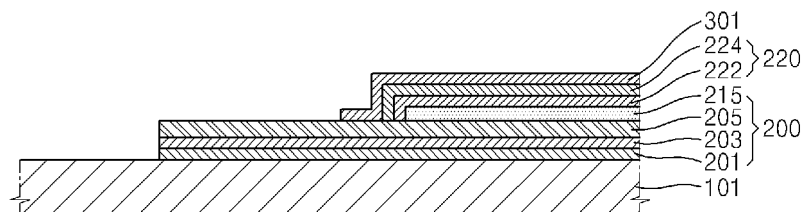
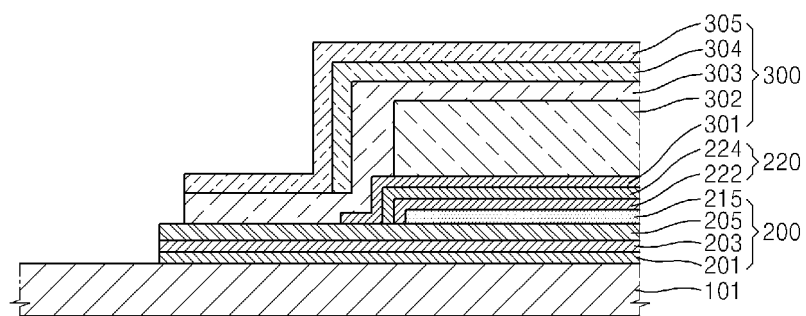


FIG. 7



REFERENCES CITED IN THE DESCRIPTION

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CPC分类号	H01L27/3244 H01L51/5246 H01L51/5256 H01L27/00 H05B33/04 H01L27/3272 H01L51/00 H01L51/56		
优先权	1020120131115 2012-11-19 KR		
其他公开文献	EP2733763A3 EP2733763A2		
外部链接	Espacenet		

摘要(译)

公开了一种有机发光显示系统及其制造方法。一方面，有机发光显示系统包括基板（101），显示单元（200），该显示单元（200）在基板（101）上限定有源区（AA）并且包括多个薄膜晶体管（TFT），密封层（300），其密封显示单元（200），并具有依次层叠至少第一无机膜（301），第一有机膜（302）和第二无机膜（303）的堆叠结构。堆叠。TFT包括有源层（202），栅电极（204），源电极（206），漏电极（207）以及设置在栅电极（204）和栅电极之间的层间绝缘膜（205）。源电极（206）和栅电极（204）与漏电极（207）之间，其中第二无机膜（303）直接接触有源区（AA）外部的层间绝缘膜（205）。因此，在各种实施例中，由于防止了薄膜封装层的无机层破裂，所以可以减少或防止外部湿气或氧气渗透到显示器的有源区域中。

FIG. 1

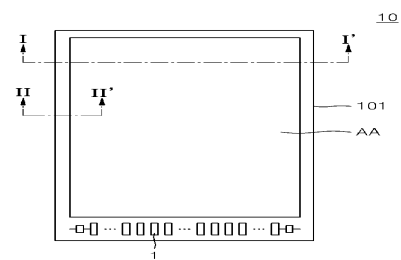


FIG. 2

